140W, 28V High Power RF LDMOS FETs

Description

The MX0514 is a 140-watt capable, highly rugged, unmatched LDMOS FET, designed for wide-band commercial and industrial applications with frequencies HF to 1 GHz.

•Typical Performance (On Innogration fixture with device soldered):

 V_{DD} = 28 Volts, I_{DQ} = 800 mA, CW.

Frequency	Gp (dB)	P _{-1dB} (W)	η _D @P ₋₁ (%)	
1000 MHz	18	140	60	

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- · Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- · Pb-free, RoHS-compliant

Suitable Applications

- 2-30MHz (HF or Short wave communication)
- 30-88MHz (Ground communication)
- 54-88MHz (TV VHF I)
- 88-108MHz (FM)
- 118 -140MHz (Avionics)

- 136-174MHz (Commercial ground communication)
- 160-230MHz (TV VHF III)
- 30-512MHz (Jammer, Ground/Air communication)
- 470-860MHz (TV UHF)
- 100kHz 1000MHz (ISM, instrumentation)

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
DrainSource Voltage	V _{DSS}	+95	Vdc
GateSource Voltage	$V_{\sf GS}$	-10 to +10	Vdc
Operating Voltage	V_{DD}	+40	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	Tc	+150	°C
Operating Junction Temperature	TJ	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Thermal Resistance, Junction to Case	Davis	0.4	20044	
T _C = 85°C, T _J =200°C, DC test	Rejc	0.4	°C/W	

Table 3. ESD Protection Characteristics

Test Methodology	Class		
Human Body Model (per JESD22A114)	Class 2		

Table 4. Electrical Characteristics (T_A = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
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DC Characteristics (per half section)

Drain-Source Voltage	.,	0.5			.,
V _{GS} =0, I _{DS} =1.0mA	$V_{(BR)DSS}$	95			V
Zero Gate Voltage Drain Leakage Current	1			1	μА
$(V_{DS} = 75V, V_{GS} = 0 V)$	I _{DSS}			ı	μΑ
Zero Gate Voltage Drain Leakage Current				1	^
$(V_{DS} = 28 \text{ V}, V_{GS} = 0 \text{ V})$	DSS			ı	μΑ
GateSource Leakage Current				1	^
$(V_{GS} = 10 \text{ V}, V_{DS} = 0 \text{ V})$	I _{GSS}			ı	μΑ
Gate Threshold Voltage	\/ (4b)		2.2		V
$(V_{DS} = 28V, I_D = 400 \mu A)$	$V_{GS}(th)$		2.2		V
Gate Quiescent Voltage	$V_{GS(Q)}$		3.1		V
$(V_{DD} = 28 \text{ V}, I_D = 800 \text{ mA}, \text{Measured in Functional Test})$	V GS(Q)	·	3.1		V
Common Source Input Capacitance	C _{ISS}		70		pF
$(V_{GS} = 0V, V_{DS} = 28 V, f = 1 MHz)$	OISS		70		ρi
Common Source Output Capacitance			29.5		۲.
(V _{GS} = 0V, V _{DS} =28 V, f = 1 MHz)	C _{oss}		29.5		pF
Common Source Feedback Capacitance			1.1		pF
$(V_{GS} = 0V, V_{DS} = 28 V, f = 1 MHz)$	C _{RSS}	∪ RSS			ρг

Functional Tests (In Demo Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 800 mA, f = 1000 MHz, CW Signal Measurements.

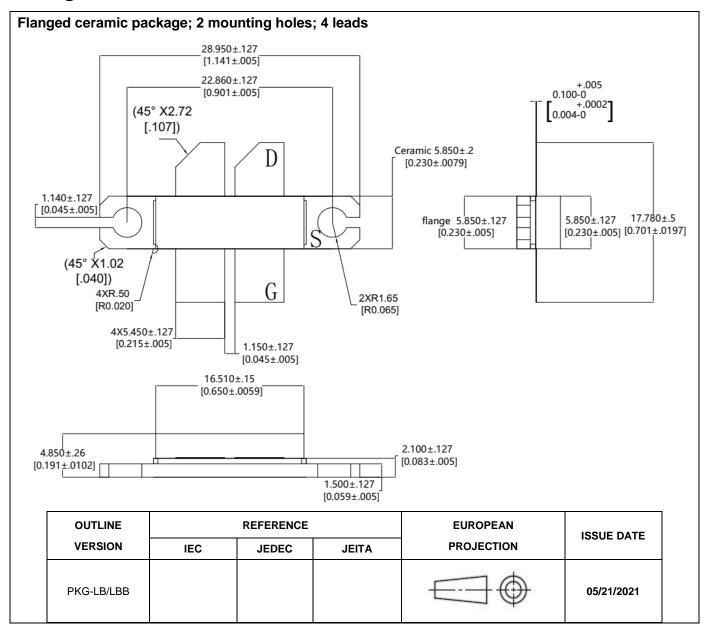
Power Gain	Gp	 18	 dB
Drain Efficiency@P1dB	η _D	 60	 %
1 dB Compression Point	P _{-1dB}	 140	 W
Input Return Loss	IRL	 -7	 dB

Load Mismatch (In Innogration Test Fixture, 50 ohm system): $V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 800 \text{ mA}$, f = 1000 MHz

VSWR 20:1 at 140W pulse CW Output Power	No Device Degradation
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MX0514 LDMOS TRANSISTOR

Package Outline



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Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2017/10/13	Rev 1.0	Product Datasheet Creation
2021/5/21	Rev 1.1	Package outline update

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